

# Radar Pulsed Power Transistor 75W, 2.7-3.1 GHz, 300µs Pulse, 10% Duty

# M/A-COM Products Released, 10 Aug 07

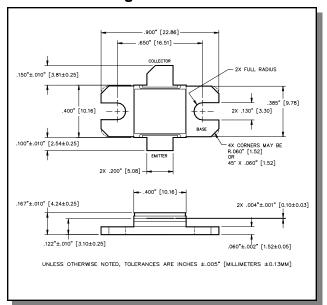
#### **Features**

- · NPN silicon microwave power transistors
- Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- · Internal input and output impedance matching
- · Hermetic metal/ceramic package
- RoHS compliant

## Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V <sub>CES</sub>	65	V
Emitter-Base Voltage	$V_{EBO}$	3.0	V
Collector Current (Peak)	Ic	7.0	Α
Power Dissipation @ +25°C	P <sub>TOT</sub>	220	W
Storage Temperature	T <sub>STG</sub>	-65 to +200	°C
Junction Temperature	$T_J$	200	°C

#### **Outline Drawing**



## Electrical Specifications: T<sub>C</sub> = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA		BV <sub>CES</sub>	65	-	V
Collector-Emitter Leakage Current	V <sub>CE</sub> = 36V		I <sub>CES</sub>	-	7.5	mA
Thermal Resistance	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	R <sub>TH(JC)</sub>	-	0.8	°C/W
Output Power	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	P <sub>IN</sub>	-	13.5	W
Power Gain	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	G₽	7.45	-	dB
Collector Efficiency	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	ης	38	i	%
Input Return Loss	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	VSWR-T	-	3:1	-
Load Mismatch Stability	Vcc = 36V, Pout =75W	F = 2.7, 2.9, 3.1 GHz	VSWR-S	-	1.5:1	-

Commitment to produce in volume is not qua

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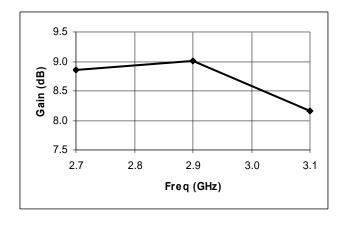


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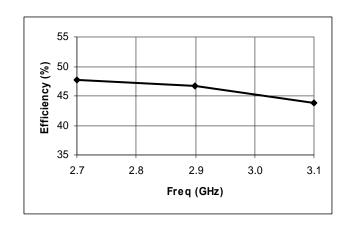
#### **Typical RF Performance**

Freq. (GHz)	Pin (W)	Pout (W)	Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)
2.7	9.8	75	8.86	4.40	47.8	-11.0	S	Р
2.9	9.4	75	9.01	4.50	46.7	-18.5	S	Р
3.1	11.5	75	8.16	4.80	43.8	-17.7	S	Р

## Gain vs. Frequency



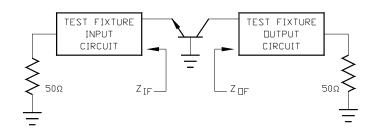
## Collector Efficiency vs. Frequency



#### **RF Test Fixture Impedance**

typical. Mechanical outline has been fixed. Engineering samples Commitment to produce in volume is not guaranteed.

F (GHz)	Z <sub>IF</sub> (Ω)	Z <sub>OF</sub> (Ω)		
2.7	6.9 - j12.2	4.5 - j6.8		
2.9	6.0 - j11.7	3.9 - j6.1		
3.1	5.2 - j10.0	3.4 - j4.8		



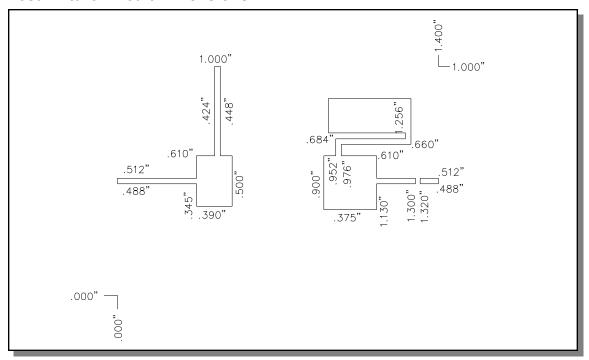
Solutions has under development. Performance is based on engineering tests. Specifications are

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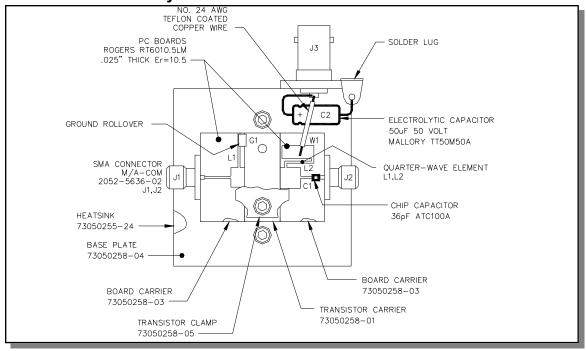


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#### **Test Fixture Circuit Dimensions**



# **Test Fixture Assembly**



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